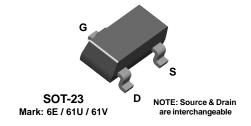


2N5460 2N5461 2N5462 MMBF5460 MMBF5461 MMBF5462





P-Channel General Purpose Amplifier

This device is designed primarily for low level audio and general purpose applications with high impedance signal sources. Sourced from Process 89.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units	
V_{DG}	Drain-Gate Voltage	- 40	V	
V _{GS}	Gate-Source Voltage	40	V	
I _{GF}	Forward Gate Current	10	mA	
T _J ,T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C	

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max		Units
		2N5460-5462	*MMBF5460-5462	
P_D	Total Device Dissipation Derate above 25°C	350 2.8	225 1.8	mW mW/°C
R _{θJC}	Thermal Resistance, Junction to Case	125		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	556	°C/W

^{*}Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

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2N5460/5461/5462/MMBF5460/5461/5462, Rev A

P-Channel General Purpose Amplifier

60

115

nV/√Hz

(continued)

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
						•
OFF CHA	RACTERISTICS					
$V_{(BR)GSS}$	Gate-Source Breakdown Voltage	$I_G = 10 \mu\text{A}, V_{DS} = 0$	40			V
Igss	Gate Reverse Current	V _G S = 20 V, V _D S = 0			5.0	nA
		$V_{GS} = 20 \text{ V}, V_{DS} = 0, T_A = 100^{\circ}\text{C}$			1.0	μΑ
$V_{GS(off)}$	Gate-Source Cutoff Voltage	$V_{DS} = 15 \text{ V}, I_D = 1.0 \mu\text{A}$ 5460	0.75		6.0	V
		5461	1.0 1.8		7.5 9.0	V
\/	Cata Cauraa Valtaga	Vps = 15 V, lp = 0.1 mA 5460				V
Vgs	Gate-Source Voltage	V _{DS} = 15 V, I _D = 0.1 mA 5460 V _{DS} = 15 V, I _D = 0.2 mA 5461	0.5 0.8		4.0 4.5	V
		V _{DS} = 15 V, I _D = 0.2 mA	1.5		6.0	v
IDSS	Zero-Gate Voltage Drain Current*	V _{DS} = 15 V, V _{GS} = 0 5460 5461	- 1.0 - 2.0		- 5.0 - 9.0 - 16	mA mA
SMALL SI	GNAL CHARACTERISTICS	5462	- 4.0		- 10	mA
	Forward Transfer Conductance	V _{DS} = 15 V, V _{GS} = 0, f = 1.0 kHz				
g fs	Torward Transier Conductance	5460	1000		4000	μmhos
		5461	1500		5000	μmhos
		5462	2000		6000	μmhos
gos	Output Conductance	V _{DS} = 15 V, V _{GS} = 0, f = 1.0 kHz			75	μmhos
	Input Capacitance	V _{DS} = 15 V, V _{GS} = 0, f = 1.0 MHz		5.0	7.0	pF
Ciss	·	V _{DS} = 15 V, V _{GS} = 0, f = 1.0 MHz				
	Reverse Transfer Capacitance	$V_{DS} = 15 \text{ V}, V_{GS} = 0, f = 1.0 \text{ MHz}$		1.0	2.0	pF
C _{iss} C _{rss} NF	' '	V _{DS} = 15 V, V _{GS} = 0,		1.0	2.0	pF dB
Crss	Reverse Transfer Capacitance					

V_{DS} = 15 V, V_{GS} = 0, f = 100 Hz, BW = 1.0 Hz

en

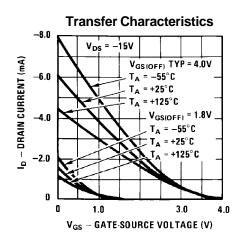
Equivalent Short-Circuit Input Noise Voltage

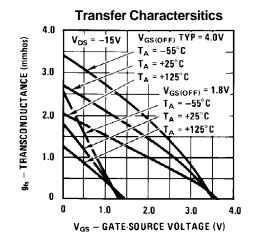
^{*}Pulse Test: Pulse Width ≤300 ms, Duty Cycle ≤2%

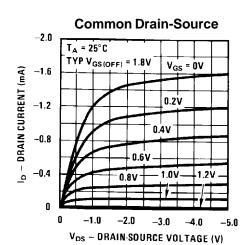
P-Channel General Purpose Amplifier

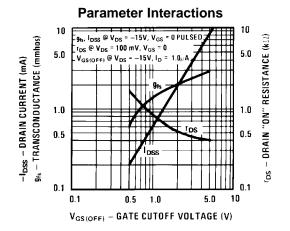
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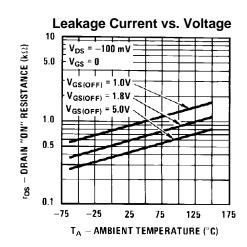
Typical Characteristics (continued)

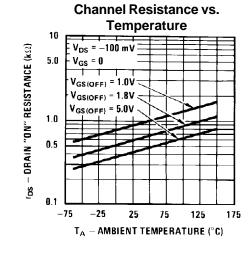








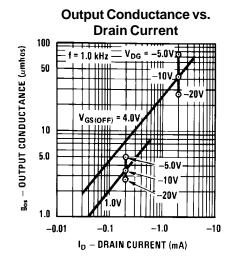


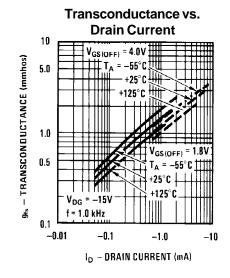


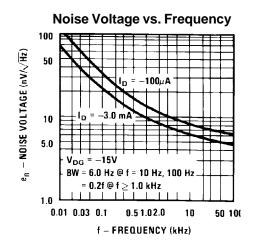
P-Channel General Purpose Amplifier

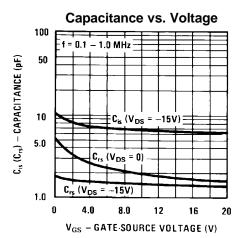
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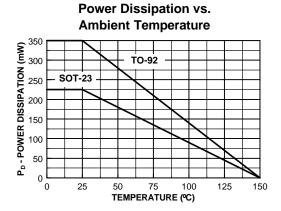
Typical Characteristics (continued)











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Rev. H2